MC74ACT241

Octal Buffer/Line Driver with 3-State Outputs

The MC74ACT241 is an octal buffer and line driver designed to be employed as a memory address driver, clock driver and bus oriented transmitter or receiver which provides improved PC board density.

- 3–State Outputs Drive Bus Lines or Buffer Memory Address Registers
- Outputs Source/Sink 24 mA
- TTL Compatible Inputs

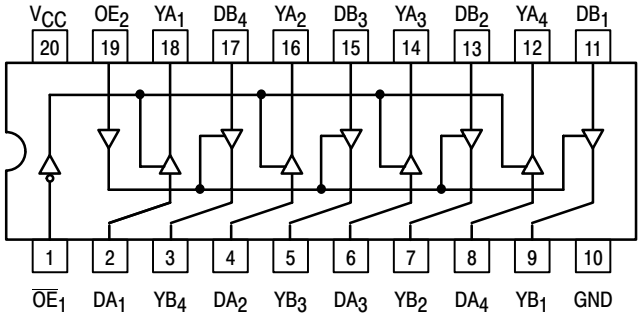

Figure 1. Pinout: 20–Lead Packages Conductors
(Top View)

TRUTH TABLE

Inputs		Outputs
$\overline{OE}_1$	D	(Pins 12, 14, 16, 18)
L	L	L
L	H	H
H	X	Z

H = HIGH Voltage Level
L = LOW Voltage Level
X = Immaterial
Z = High Impedance

TRUTH TABLE

Inputs		Outputs
OE_2	D	(Pins 3, 5, 7, 9)
H	L	L
H	H	H
L	X	Z

H = HIGH Voltage Level
L = LOW Voltage Level
X = Immaterial
Z = High Impedance

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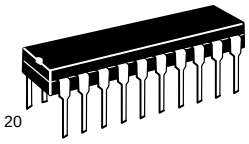
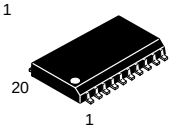
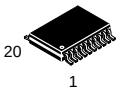


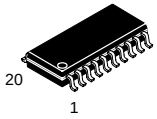
PDIP–20
N SUFFIX
CASE 738



SO–20
DW SUFFIX
CASE 751



TSSOP–20
DT SUFFIX
CASE 948E



EIAJ–20
M SUFFIX
CASE 967

ORDERING INFORMATION

Device	Package	Shipping
MC74ACT241N	PDIP–20	18 Units/Rail
MC74ACT241DW	SOIC–20	38 Units/Rail
MC74ACT241DWR2	SOIC–20	1000 Tape & Reel
MC74ACT241DT	TSSOP–20	75 Units/Rail
MC74ACT241DTR2	TSSOP–20	2500 Tape & Reel
MC74ACT241M	EIAJ–20	40 Units/Rail
MC74ACT241MEL	EIAJ–20	2000 Tape & Reel

DEVICE MARKING INFORMATION

See general marking information in the device marking section on page 302 of this data sheet.

June, 2001 – Rev. 2
Publication Order Number:
MC74ACT241/D

MAXIMUM RATINGS (Note 1)

Symbol	Parameter		Value	Unit
V_{CC}	DC Supply Voltage		−0.5 to +7.0	V
V_I	DC Input Voltage		$-0.5 \le V_I \le V_{CC} + 0.5$	V
V_O	DC Output Voltage	(Note 2)	$-0.5 \le V_O \le V_{CC} + 0.5$	V
I_{IK}	DC Input Diode Current		±20	mA
I_{OK}	DC Output Diode Current		±50	mA
I_O	DC Output Sink/Source Current		±50	mA
I_{CC}	DC Supply Current per Output Pin		±50	mA
I_{GND}	DC Ground Current per Output Pin		±100	mA
T_{STG}	Storage Temperature Range		−65 to +150	°C
T_L	Lead temperature, 1 mm from Case for 10 Seconds		260	°C
T_J	Junction temperature under Bias		+150	°C
θ_{JA}	Thermal resistance	PDIP SOIC TSSOP	67 96 128	°C/W
P_D	Power Dissipation in Still Air at 85°C	PDIP SOIC TSSOP	750 500 450	mW
MSL	Moisture Sensitivity		Level 1	
F_R	Flammability Rating	Oxygen Index: 30% – 35%	UL–94–VO (0.125 in)	
V_{ESD}	ESD Withstand Voltage	Human Body Model (Note 3) Machine Model (Note 4) Charged Device Model (Note 5)	> 2000 > 200 > 1000	V
$I_{Latch–Up}$	Latch–Up Performance	Above V_{CC} and Below GND at 85°C (Note 6)	±100	mA

1. Absolute maximum continuous ratings are those values beyond which damage to the device may occur. Extended exposure to these conditions or conditions beyond those indicated may adversely affect device reliability. Functional operation under absolute maximum–rated conditions is not implied.
2. I_O absolute maximum rating must be observed.
3. Tested to EIA/JESD22–A114–A.
4. Tested to EIA/JESD22–A115–A.
5. Tested to JESD22–C101–A.
6. Tested to EIA/JESD78.

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter		Min	Typ	Max	Unit
V_{CC}	DC Input Voltage (Referenced to GND)		4.5		5.5	V
V_{in}, V_{out}	DC Input Voltage, Output Voltage (Referenced to GND)		0		V_{CC}	V
T_A	Operating Temperature, All Package Types		–40	25	+85	°C
t_r, t_f	Input Rise and Fall Time (Note 8)	V_{CC} = 4.5 V V_{CC} = 5.5 V	0 0	10 8.0	10 8.0	ns/V
T_J	Junction Temperature (PDIP)				140	°C
I_{OH}	Output Current – High				–24	mA
I_{OL}	Output Current – Low				24	mA

7. Unused Inputs may not be left open. All inputs must be tied to a high voltage level or low logic voltage level.
8. V_{in} from 0.8 V to 2.0 V; refer to individual Data Sheets for devices that differ from the typical input rise and fall times.

DC CHARACTERISTICS

Symbol	Parameter	V_{CC} (V)	T_A = +25°C Typ	T_A = –40°C to +85°C Guaranteed Limits		Unit	Conditions
V_{IH}	Minimum High Level Input Voltage	4.5 5.5	1.5 1.5	2.0 2.0	2.0 2.0	V V	V_{OUT} = 0.1 V or V_{CC} – 0.1 V
V_{IL}	Maximum Low Level Input Voltage	4.5 5.5	1.5 1.5	0.8 0.8	0.8 0.8	V V	V_{OUT} = 0.1 V or V_{CC} – 0.1 V
V_{OH}	Minimum High Level Output Voltage	4.5 5.5	4.49 5.49	4.4 5.4	4.4 5.4	V V	I_{OUT} = –50 μA
		4.5 5.5		3.86 4.86	3.76 4.76	V V	*V_{IN} = V_{IL} or V_{IH} –24 mA I_{OH} –24 mA
V_{OL}	Maximum Low Level Output Voltage	4.5 5.5	0.001 0.001	0.1 0.1	0.1 0.1	V V	I_{OUT} = 50 μA
		4.5 5.5		0.36 0.36	0.44 0.44	V V	*V_{IN} = V_{IL} or V_{IH} 24 mA I_{OL} 24 mA
I_{IN}	Maximum Input Leakage Current	5.5		±0.1	±1.0	μA	V_I = V_{CC}, GND
ΔI_{CCT}	Additional Maximum I_{CC}/Input	5.5	0.6		1.5	mA	V_I = V_{CC} – 2.1 V
I_{OZ}	Maximum 3–State Current	5.5		±0.5	±5.0	μA	V_I (OE) = V_{IL}, V_{IH} V_I = V_{CC}, GND V_O = V_{CC}, GND
I_{OLD} I_{OHD}	†Minimum Dynamic Output Current	5.5 5.5			75 –75	mA mA	V_{OLD} = 1.65 V Max V_{OHD} = 3.85 V Min
I_{CC}	Maximum Quiescent Supply Current	5.5		8.0	80	μA	V_{IN} = V_{CC} or GND

*All outputs loaded; thresholds on input associated with output under test.
†Maximum test duration 2.0 ms, one output loaded at a time.

AC CHARACTERISTICS t_r = t_f = 3.0 ns (For Figures and Waveforms, See Figures 2, 3, and 4.)

Symbol	Parameter	V_{CC}* (V)	T_A = +25°C, C_L = 50 pF Min	Typ	Max	T_A = –40°C to +85°C, C_L = 50 pF Min	Max	Unit
t_{PLH}	Propagation Delay Data to Output	5.0	1.5	6.5	9.0	1.5	10.0	ns
t_{PHL}	Propagation Delay Data to Output	5.0	1.5	7.0	9.0	1.5	10.0	ns
t_{PZH}	Output Enable Time	5.0	1.5	6.0	9.0	1.0	10.0	ns
t_{PZL}	Output Enable Time	5.0	1.5	7.0	10.0	1.5	11.0	ns
t_{PHZ}	Output Disable Time	5.0	1.5	8.0	10.5	1.5	11.5	ns
t_{PLZ}	Output Disable Time	5.0	2.0	7.0	10.5	1.5	11.5	ns

*Voltage Range 5.0 V is 5.0 V ±0.5 V

CAPACITANCE

Symbol	Parameter	Value Typ	Unit	Test Conditions
C_{IN}	Input Capacitance	4.5	pF	V_{CC} = 5.0 V
C_{PD}	Power Dissipation Capacitance	45	pF	V_{CC} = 5.0 V

SWITCHING WAVEFORMS

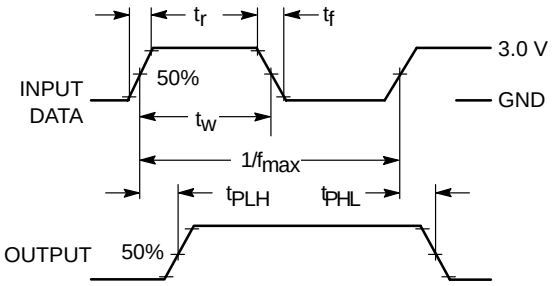


Figure 2.

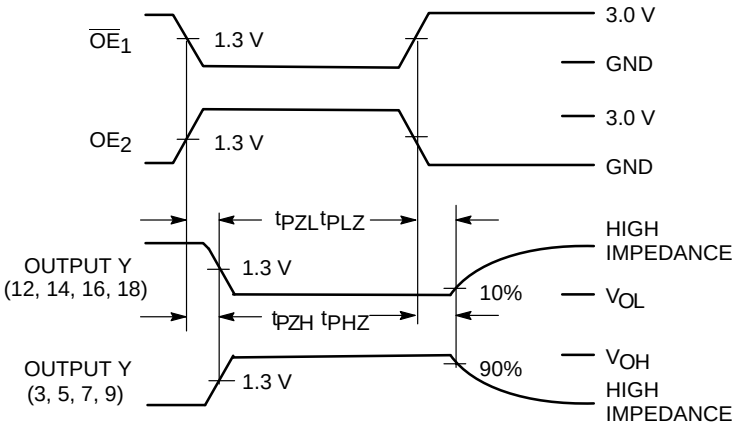
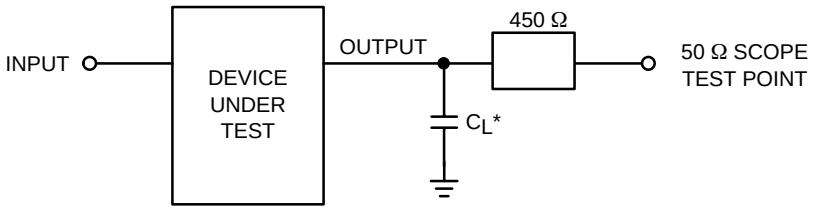


Figure 3.



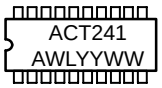
*Includes all probe and jig capacitance

Figure 4. Test Circuit

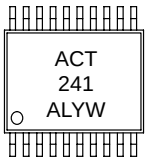
MARKING DIAGRAMS

PDIP–20

SO–20



TSSOP–20



EIAJ–20

A = Assembly Location
WL, L = Wafer Lot
YY, Y = Year
WW, W = Work Week